

## 1. Description

The KNX3302A uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching applications.

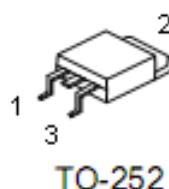
## 2. Features

- $R_{DS(on)}=3.8\text{m}\Omega(\text{typ.})$  @  $V_{GS}=4.5\text{V}$
- $V_{DS}=20\text{V}$     $I_D=85\text{A}$

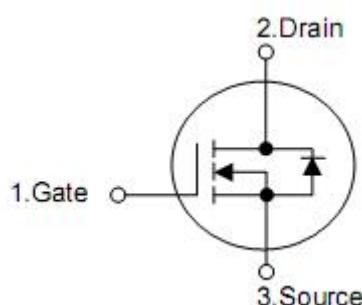
## 3. Applications

- Battery protection
- Load switch
- Uninterruptible power supply

## 4. Symbol



TO-252



Pin	Function
1	Gate
2	Drain
3	Source

## 5. Ordering Information

Part Number	Package	Brand
KND3302A	TO-252	KIA

## 6. Absolute maximum ratings

Parameter	Symbol	Rating	Units
Drain-source voltage	$V_{DS}$	20	V
Gate-source voltage	$V_{GS}$	$\pm 12$	V
Continuous drain current, $V_{GS} @ 10V$	$I_D$	85	A
$T_C=25^\circ C$		59	A
$T_C=100^\circ C$			
Pulsed drain current	$I_{DM}$	340	A
Single pulse avalanche energy <sup>(Note5)</sup>	$E_{AS}$	338	mJ
Maximum power dissipation	$P_D$	87	W
Operation junction and temperature range	$T_J, T_{STG}$	-55 to 150	$^\circ C$

## 7. Thermal characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal resistance, Junction-case	$R_{\theta JC}$	--	1.43	$^\circ C/W$

## 8. Electrical characteristics

( $T_A=25^\circ\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Drain-source breakdown voltage	$\text{BV}_{\text{DSS}}$	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=250\mu\text{A}$	20	-	-	V
Drain-source on-State resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}}=4.5\text{V}, I_{\text{D}}=25\text{A}$	-	3.8	5.5	$\text{m}\Omega$
		$V_{\text{GS}}=2.5\text{V}, I_{\text{D}}=20\text{A}$	-	5.0	7.5	
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\mu\text{A}$	0.4	0.65	1.1	V
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{DS}}=16\text{V}, V_{\text{GS}}=0\text{V}$	-	-	1	$\mu\text{A}$
Gate- Body Leakage current	$I_{\text{GSS}}$	$V_{\text{GS}}=\pm 12\text{V}, V_{\text{DS}}=0\text{V}$	-	-	$\pm 100$	nA
Forward transconductance	$g_{\text{fs}}$	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=20\text{A}$	-	20	-	S
Total gate charge	$Q_g$	$V_{\text{DS}}=10\text{V}, V_{\text{GS}}=10\text{V}$ $I_{\text{D}}=20\text{A}$	-	28	-	nC
Gate-source charge	$Q_{\text{gs}}$		-	6.5	-	
Gate-drain charge	$Q_{\text{gd}}$		-	6.4	-	
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=20\text{A},$ $R_{\text{G}}=3\Omega, V_{\text{GS}}=4.5\text{V}$	-	6.5	-	ns
Rise time	$t_r$		-	17.2	-	
Turn-off delay time	$t_{\text{d}(\text{off})}$		-	29.5	-	
Fall time	$t_f$		-	16.7	-	
Input capacitance	$C_{\text{iss}}$	$V_{\text{DS}}=10\text{V}, V_{\text{GS}}=0\text{V},$ $f=1\text{MHz}$	-	3850	-	pF
Output capacitance	$C_{\text{oss}}$		-	500	-	
Reverse transfer capacitance	$C_{\text{rss}}$		-	480	-	
Diode Forward Current <sup>(Note2)</sup>	$I_s$		-	-	85	A
Diode Forward voltage <sup>(Note3)</sup>	$V_{\text{SD}}$	$V_{\text{GS}}=0\text{V}, I_s=10\text{A}$	-	-	1.3	V
Body diode reverse recovery time	$t_{\text{rr}}$	$IF=20\text{A}, TJ=25^\circ\text{C}$ $dl/dt=100\text{A}/\mu\text{s}$ <sup>(Note3)</sup>	-	25	-	ns
Body diode reverse recovery charge	$Q_{\text{rr}}$		-	24	-	nC

Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. E<sub>AS</sub> condition :  $T_j=25^\circ\text{C}, V_{\text{DD}}=20\text{V}, V_{\text{GS}}=4.5\text{V}, L=0.5\text{mH}, I_d=26\text{A}$

## 9. Test circuits

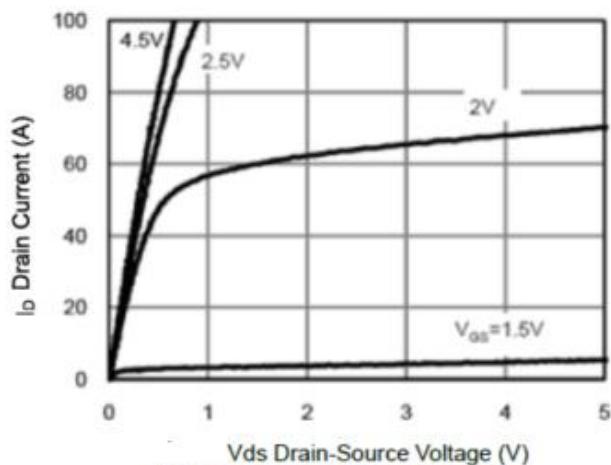


Figure 1 Output Characteristics

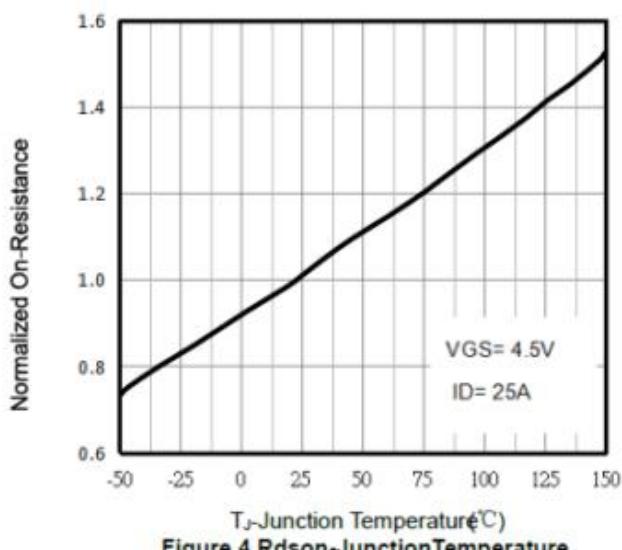


Figure 4 Rdson-JunctionTemperature

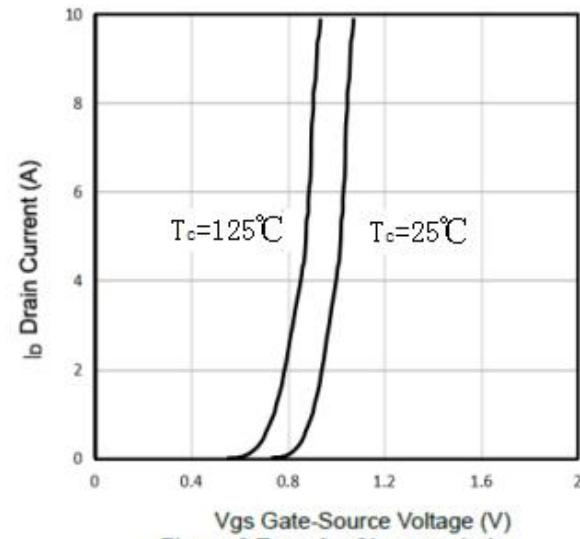


Figure 2 Transfer Characteristics

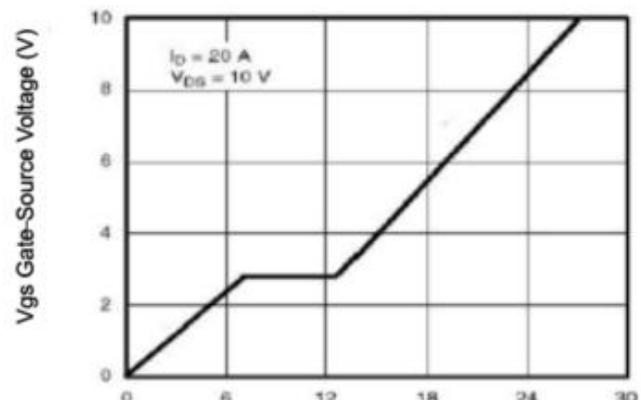


Figure 5 Gate Charge

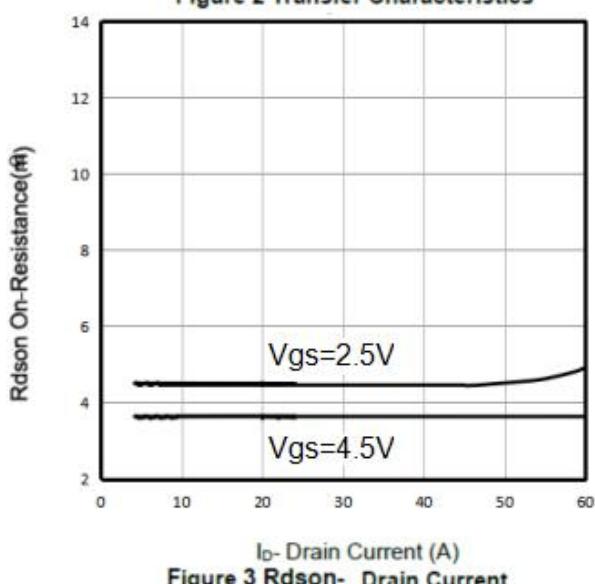


Figure 3 Rdson- Drain Current

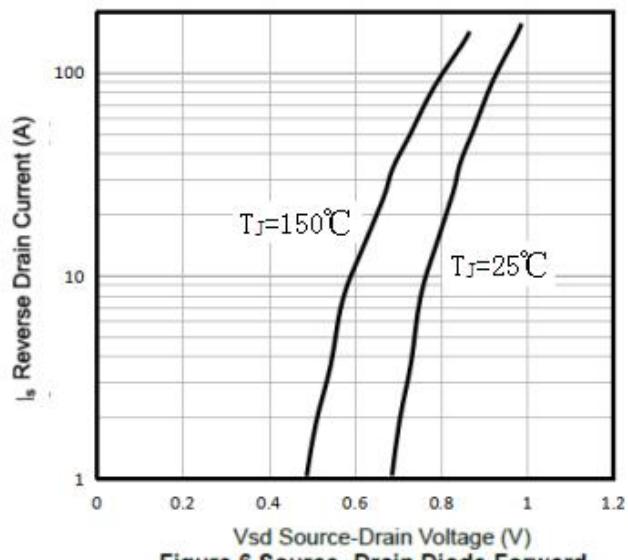


Figure 6 Source- Drain Diode Forward

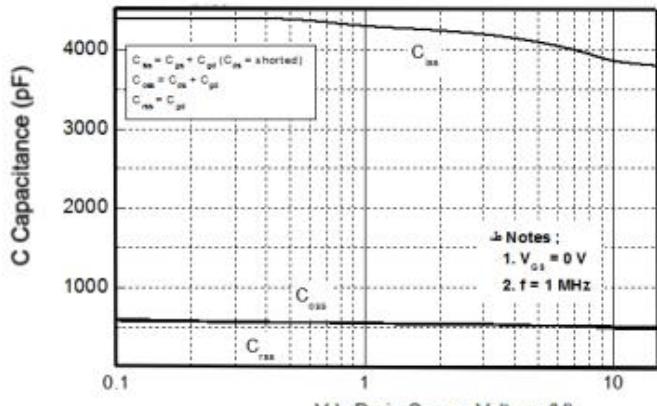


Figure 7 Capacitance vs Vds

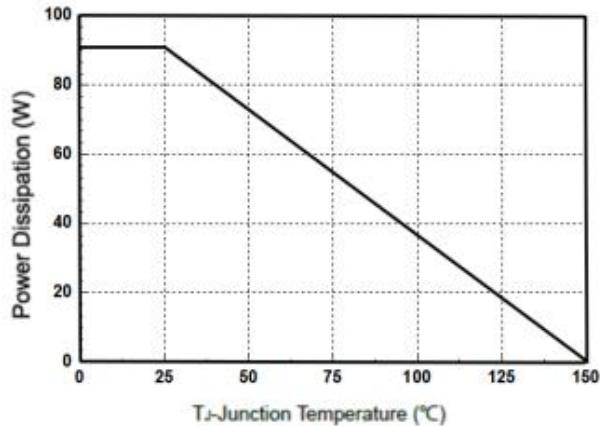


Figure 9 Power De-rating

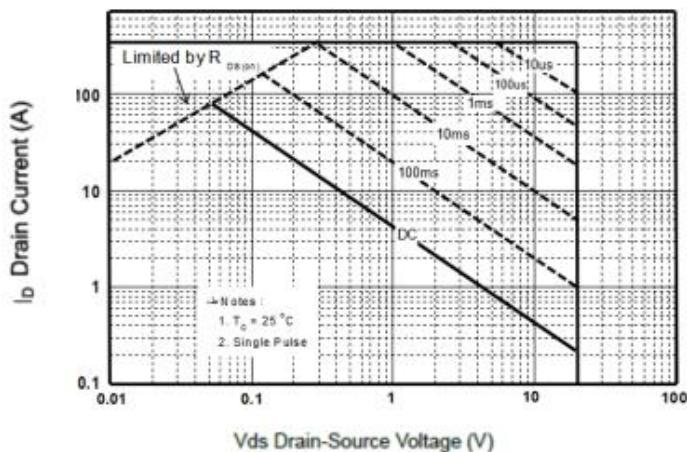


Figure 8 Safe Operation Area

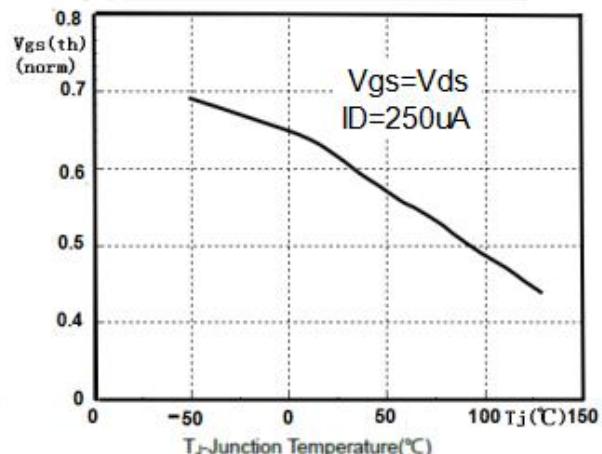
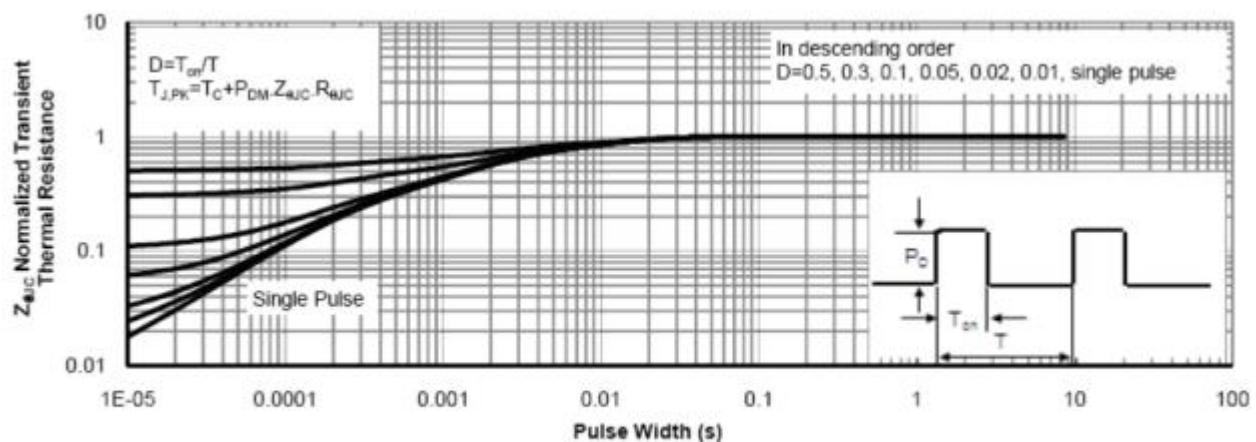


Figure 10 V<sub>gs(th)</sub> vs Junction Temperature



Square Wave Pulse Duration(sec)  
Figure 11 Normalized Maximum Transient Thermal Impedance

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